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MOSFET - Power, N-Channel, SUPERFET® III, FRFET®

650 V, 24 A, 150 mΩ

NTMT150N65S3HF

Description

SUPERFET III MOSFET is ON Semiconductor's brand−new high voltage super−junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on−resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET is very suitable for the various power systems for miniaturization and higher efficiency. SUPERFET III FRFET MOSFET's optimized reverse recovery performance of body diode can remove additional component and improve system reliability.

Features

- 700 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 121 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 43 nC)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 400 pF)
- 100% Avalanche Tested
- These Devices are Pb−Free and are RoHS Compliant

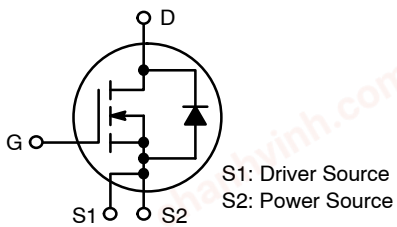
Applications

- Telecom / Server Power Supplies
- Industrial Power Supplies
- UPS / Solar
- Lighting

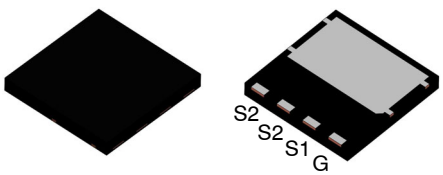
ON Semiconductor®

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V_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX
650 V	150 mΩ @ 10 V	24 A



POWER MOSFET



Power88
PQFN4 8X8 2P
CASE 483AP

MARKING DIAGRAM



NTMT150N65S3HF	= Specific Device Code
A	= Assembly Location
WL	= Wafer Lot
Y	= Year
WW	= Work Week

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		650	V
V_{GSS}	Gate to Source Voltage	– DC	±30	V
		– AC (f > 1 Hz)	±30	
I_D	Drain Current	– Continuous (T_C = 25°C)	24	A
		– Continuous (T_C = 100°C)	15.2	
I_{DM}	Drain Current	– Pulsed (Note 1)	60	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		275	mJ
I_{AS}	Avalanche Current (Note 2)		3.8	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		1.92	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		50	
P_D	Power Dissipation	(T_C = 25°C)	192	W
		– Derate Above 25°C	1.54	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		–55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8″ from Case for 5 seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse−width limited by maximum junction temperature.
2. I_{AS} = 3.8 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 12 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.65	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max., (Note 4)	45	

4. Device on 1 in^2 2−oz copper pad on 1.5 x 1.5 in. board of FR−4 material.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Reel Size	Tape Width	Shipping†
NTMT150N65S3HF	NTMT150N65S3HF	Power88	13″	13.3 mm	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	650			V
		V_{GS} = 0 V, I_D = 1 mA, T_J = 150°C	700			V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 10 mA, Referenced to 25°C		0.62		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V			10	μA
		V_{DS} = 520 V, T_C = 125°C		10		
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V			±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 0.54 mA	3.0		5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 12 A		121	150	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 12 A		14		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 400 V, V_{GS} = 0 V, f = 1 MHz		1985		pF
C_{oss}	Output Capacitance			40		pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V		400		pF
$C_{oss(er.)}$	Energy Related Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V		71		pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	V_{DS} = 400 V, I_D = 12 A, V_{GS} = 10 V (Note 5)		43		nC
Q_{gs}	Gate to Source Gate Charge			13		nC
Q_{gd}	Gate to Drain “Miller” Charge			17		nC
ESR	Equivalent Series Resistance	f = 1 MHz		3.1		Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400 V, I_D = 12 A, V_{GS} = 10 V R_g = 4.7 Ω (Note 5)		24		ns
t_r	Turn-On Rise Time			12		ns
$t_{d(off)}$	Turn-Off Delay Time			60		ns
t_f	Turn-Off Fall Time			3.1		ns
SOURCE-DRAIN DIODE CHARACTERISTICS						
I_S	Maximum Continuous Source to Drain Diode Forward Current				24	A
I_{SM}	Maximum Pulsed Source to Drain Diode Forward Current				60	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 12 A			1.3	V
t_{rr}	Reverse Recovery Time	V_{DD} = 400 V, I_{SD} = 12 A, dI_F/dt = 100 A/μs		80		ns
Q_{rr}	Reverse Recovery Charge			285		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Essentially independent of operating temperature typical characteristics.

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TYPICAL CHARACTERISTICS

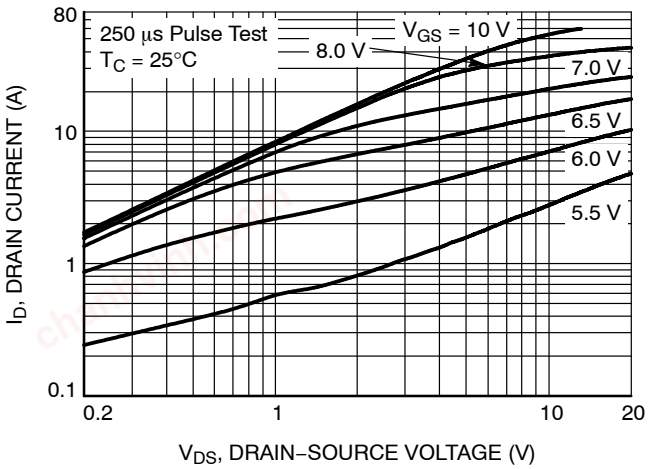


Figure 1. On−Region Characteristics

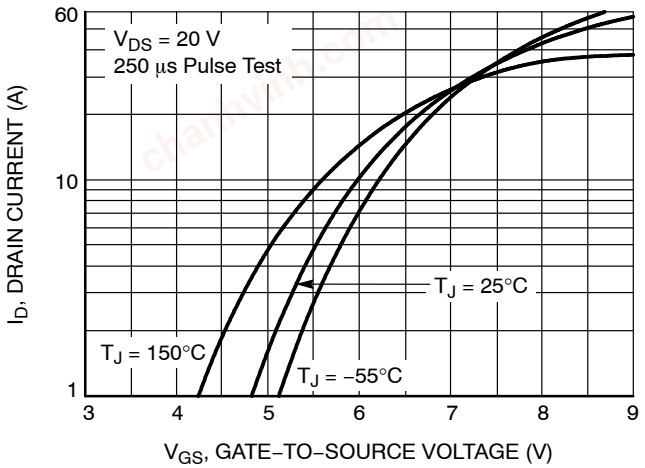


Figure 2. Transfer Characteristics

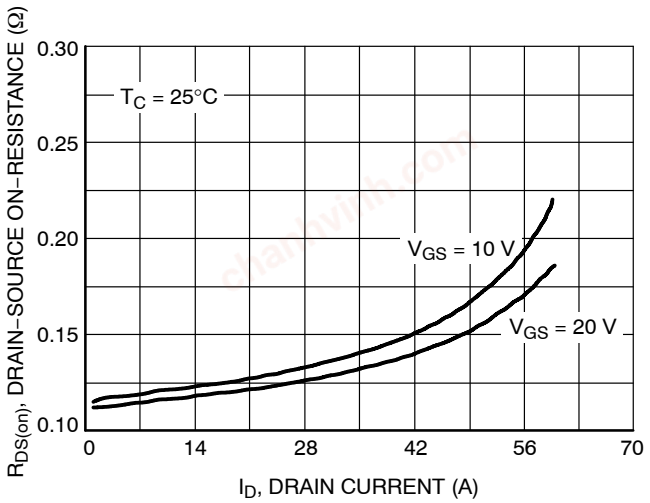


Figure 3. On−Resistance Variation vs. Drain Current and Gate Voltage

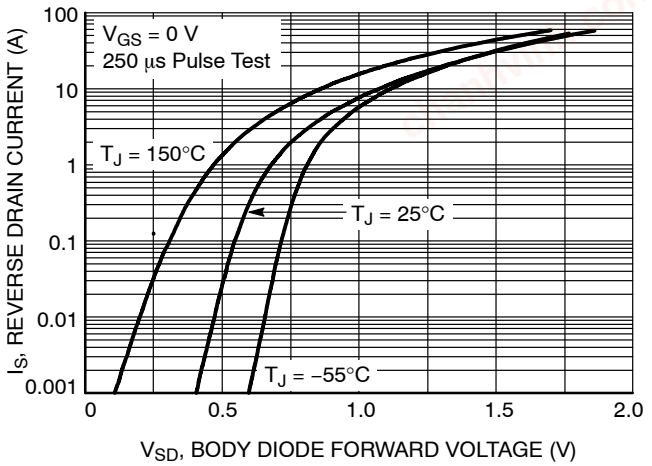


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

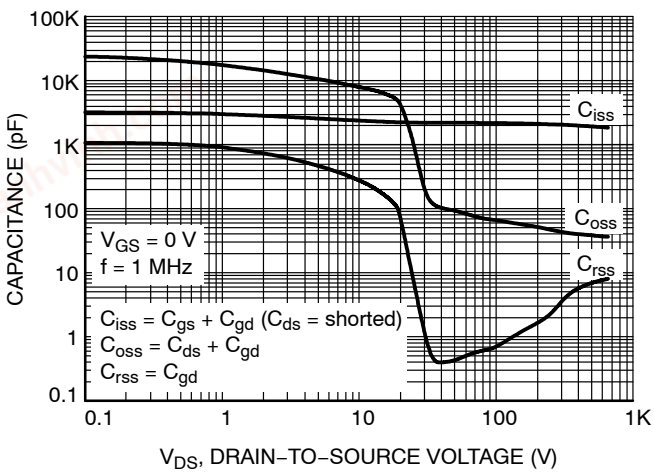


Figure 5. Capacitance Characteristics

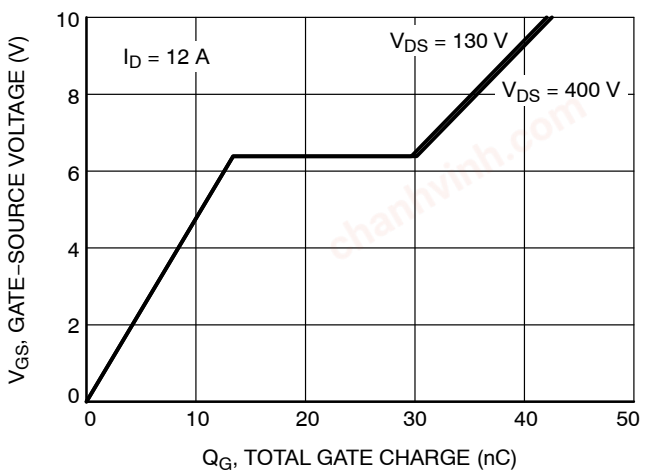


Figure 6. Gate Charge Characteristics

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TYPICAL CHARACTERISTICS

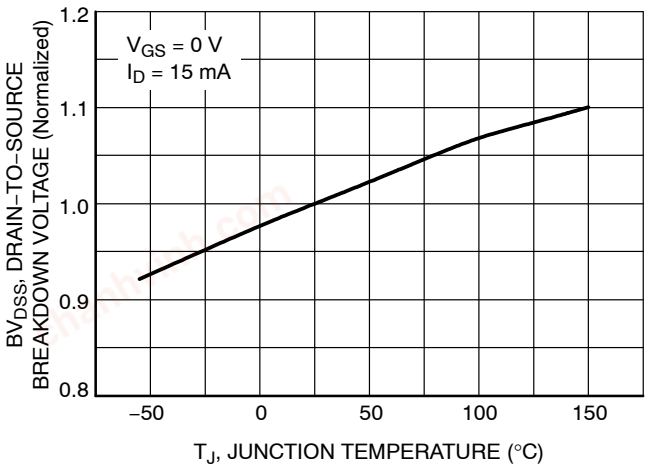


Figure 7. Breakdown Voltage Variation vs. Temperature

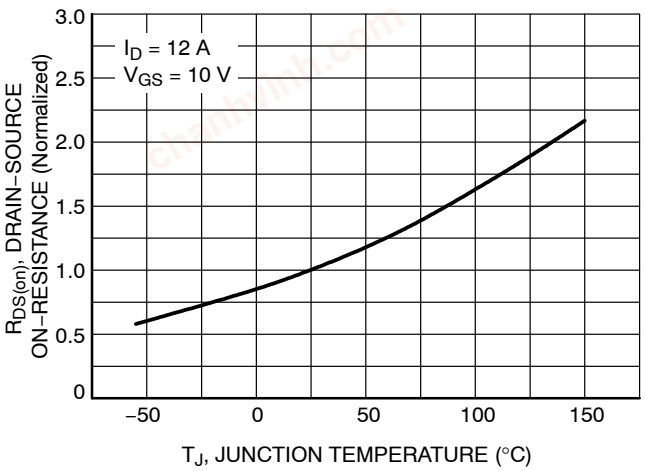


Figure 8. On−Resistance Variation vs. Temperature

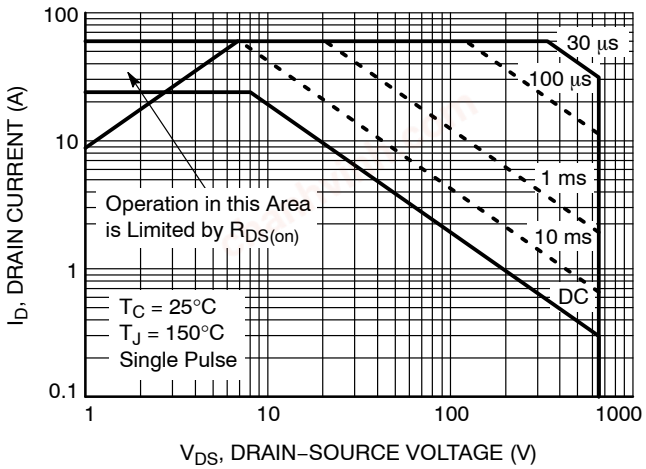


Figure 9. Maximum Safe Operating Area

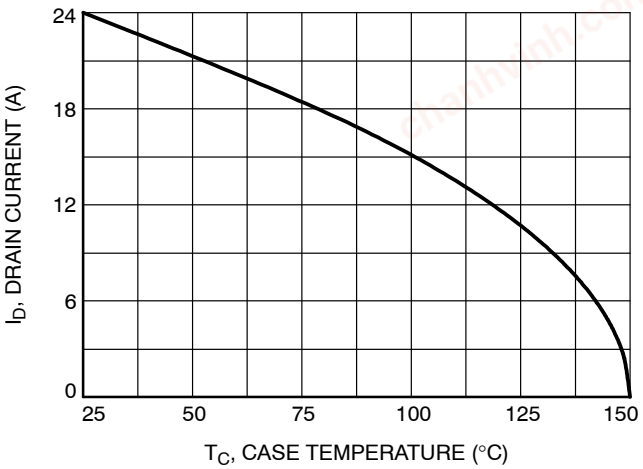


Figure 10. Maximum Drain Current vs. Case Temperature

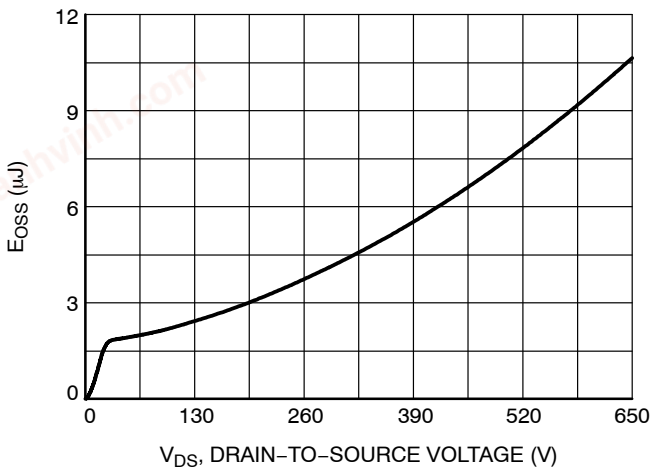


Figure 11. E_{OSS} vs. Drain−to−Source Voltage

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TYPICAL CHARACTERISTICS

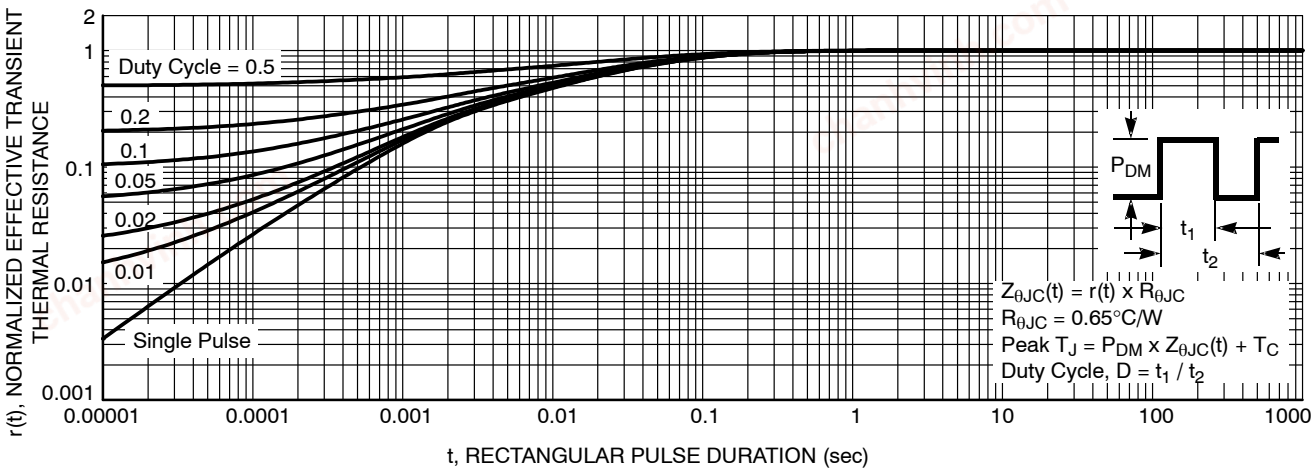


Figure 12. Transient Thermal Response Curve

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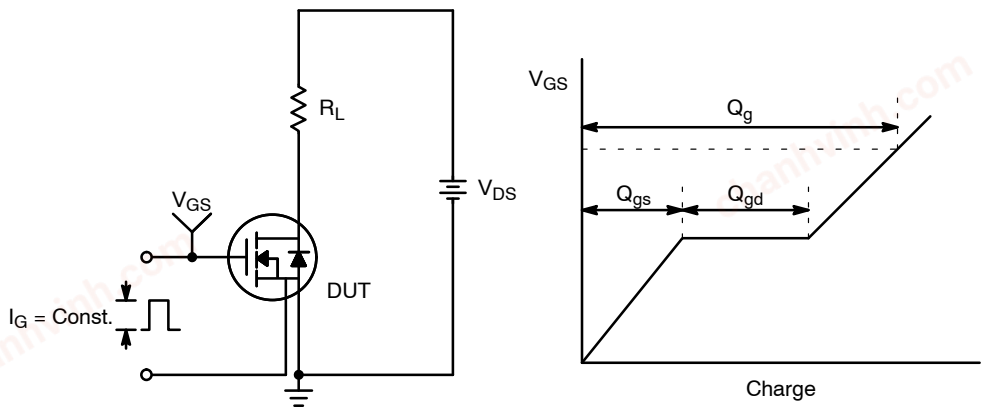


Figure 13. Gate Charge Test Circuit & Waveform

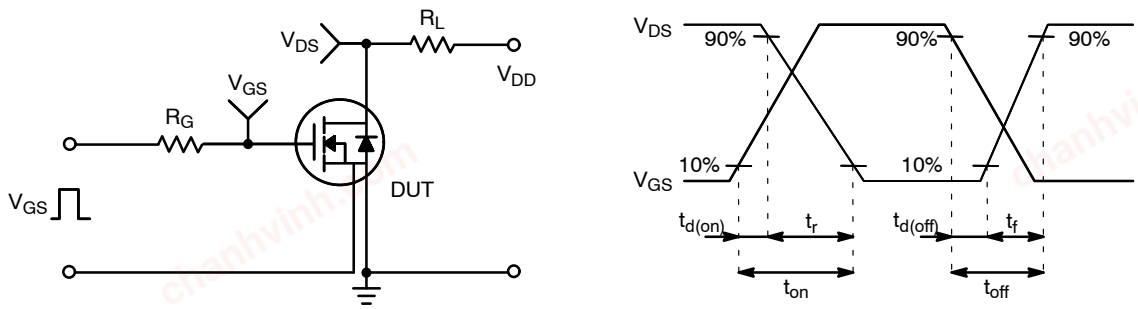


Figure 14. Resistive Switching Test Circuit & Waveforms

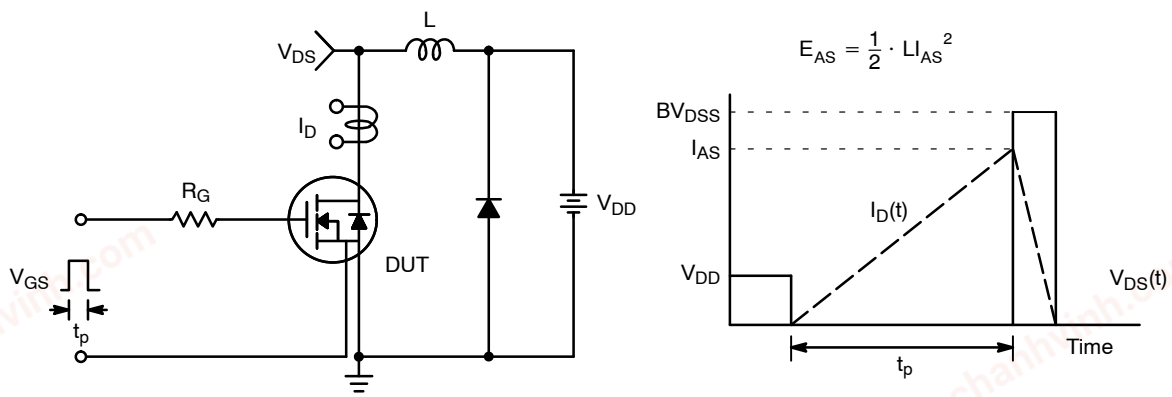


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

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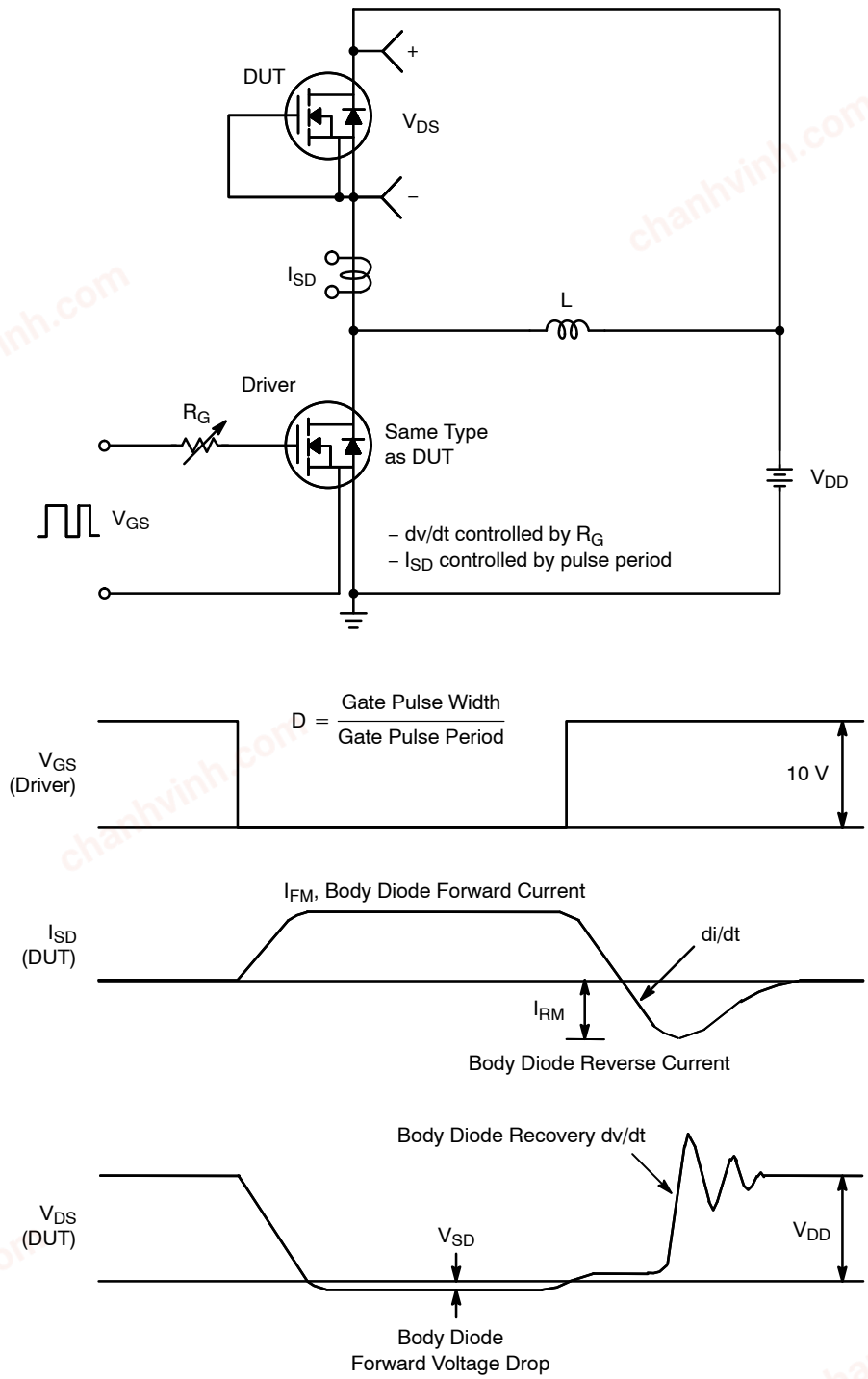


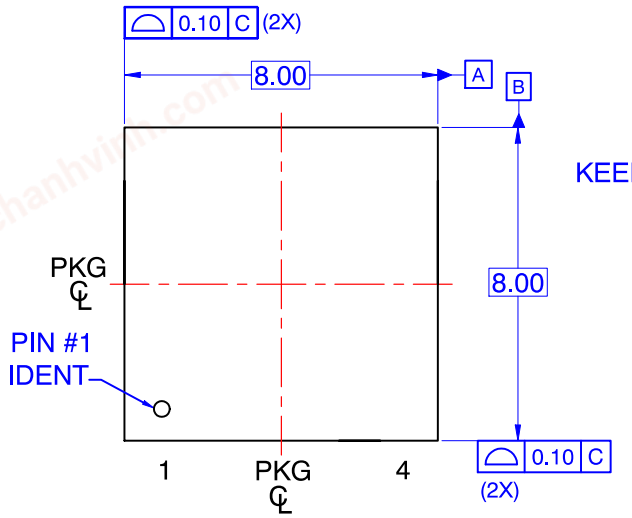
Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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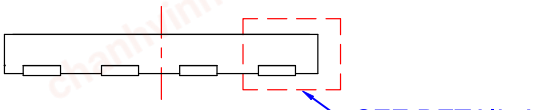
PACKAGE DIMENSIONS

PQFN4 8X8, 2P
CASE 483AP
ISSUE O

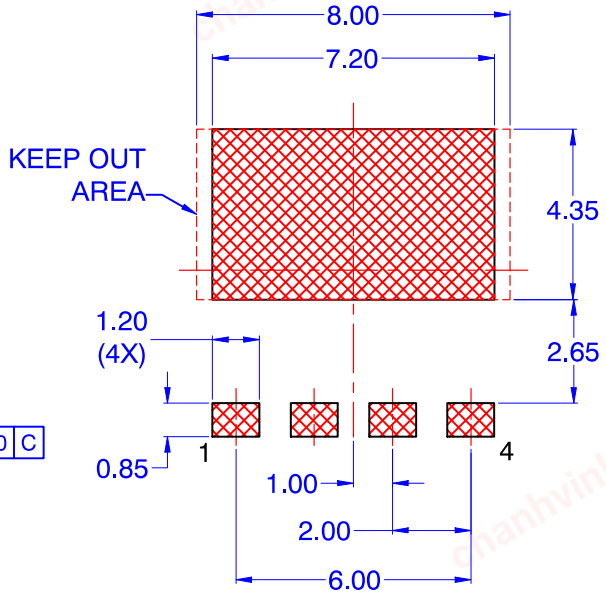
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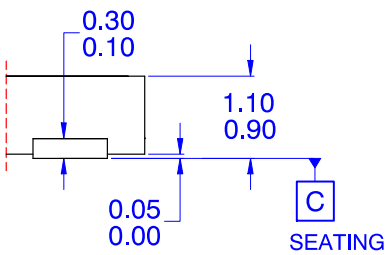
TOP VIEW



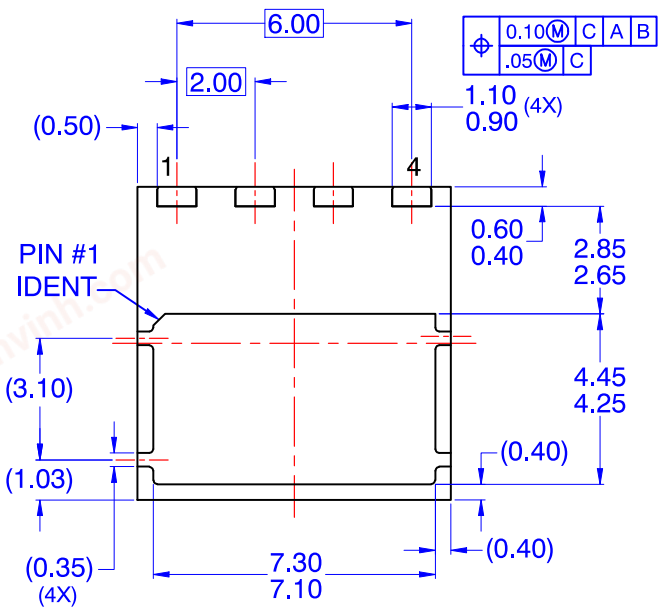
FRONT VIEW



LAND PATTERN
RECOMMENDATION



DETAIL A
SCALE: 2X



BOTTOM VIEW

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B) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR PROTRUSIONS.
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